

Phase Control Thyristors (Hockey-PUK Version), 2310 A



K-PUK (A-24)

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case K-PUK (A-24)
- High profile hockey PUK
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

PRIMARY CHARACTERISTICS

$I_{T(AV)}$	2310 A
V_{DRM}/V_{RRM}	400 V, 600 V
V_{TM}	1.44 V
I_{GT}	100 mA
T_J	-40 °C to +125 °C
Package	K-PUK (A-24)
Circuit configuration	Single SCR

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$		2310	A
	T_{hs}	55	°C
$I_{T(RMS)}$		4150	A
	T_{hs}	25	°C
I_{TSM}	50 Hz	42 500	A
	60 Hz	44 500	
I^2t	50 Hz	9027	kA ² s
	60 Hz	8240	
V_{DRM}/V_{RRM}		400 to 600	V
t_q	Typical	200	μs
T_J		-40 to +125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{DRM}/V_{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I_{DRM}/I_{RRM} MAXIMUM AT $T_J = T_J$ MAXIMUM mA
VS-ST1280C..K	04	400	500	100
	06	600	700	



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current at heatsink temperature	I _{T(AV)}	180° conduction, half sine wave Double side (single side) cooled		2310 (885)	A	
				55 (85)	°C	
Maximum RMS on-state current	I _{T(RMS)}	25 °C heatsink temperature double side cooled		4150		
Maximum peak, one-cycle non-repetitive surge current	I _{TSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	42 500	A
		t = 8.3 ms			44 500	
		t = 10 ms	100 % V _{RRM} reapplied		35 700	
		t = 8.3 ms			37 400	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		9027	kA ² s
		t = 8.3 ms			8241	
		t = 10 ms	100 % V _{RRM} reapplied		6383	
		t = 8.3 ms			5828	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied		90 270	kA ² √s	
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum		0.83	V	
High level value of threshold voltage	V _{T(TO)2}	(I > π × I _{T(AV)}), T _J = T _J maximum		0.90		
Low level value of on-state slope resistance	r _{t1}	(16.7 % × π × I _{T(AV)}) < I < π × I _{T(AV)} , T _J = T _J maximum		0.077	mΩ	
High level value of on-state slope resistance	r _{t2}	(I > π × I _{T(AV)}), T _J = T _J maximum		0.068		
Maximum on-state voltage	V _{TM}	I _{pk} = 8000 A, T _J = T _J maximum, t _p = 10 ms sine pulse		1.44	V	
Maximum holding current	I _H	T _J = 25 °C, anode supply 12 V resistive load		600	mA	
Typical latching current	I _L			1000		

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	di/dt	Gate drive 20 V, 20 Ω, $t_r \leq 1$ μs $T_J = T_J$ maximum, anode voltage ≤ 80 % V_{DRM}	1000	A/μs
Typical delay time	t_d	Gate current 1 A, $di_g/dt = 1$ A/μs $V_d = 0.67$ % V_{DRM} , $T_J = 25$ °C	1.9	μs
Typical turn-off time	t_q	$I_{TM} = 550$ A, $T_J = T_J$ maximum, $di/dt = 40$ A/μs, $V_R = 50$ V, $dV/dt = 20$ V/μs, gate 0 V 100 Ω, $t_p = 500$ μs	200	

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/μs
Maximum peak reverse and off-state leakage current	I_{RRM}, I_{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA

**TRIGGERING**

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS
			TYP.	MAX.	
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	16		W
Maximum average gate power	$P_{G(AV)}$	$T_J = T_J$ maximum, $f = 50$ Hz, $d\% = 50$	3		
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum, $t_p \leq 5$ ms	3.0		A
Maximum peak positive gate voltage	$+V_{GM}$		20		V
Maximum peak negative gate voltage	$-V_{GM}$		5.0		
DC gate current required to trigger	I_{GT}	$T_J = -40$ °C	200	-	mA
		$T_J = 25$ °C	100	200	
		$T_J = 125$ °C	50	-	
DC gate voltage required to trigger	V_{GT}	$T_J = -40$ °C	1.4	-	V
		$T_J = 25$ °C	1.1	3.0	
		$T_J = 125$ °C	0.9	-	
DC gate current not to trigger	I_{GD}	$T_J = T_J$ maximum	10		mA
DC gate voltage not to trigger	V_{GD}		0.25		V

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating temperature range	T_J		-40 to 125	°C
Maximum storage temperature range	T_{Stg}		-40 to 150	
Maximum thermal resistance, junction to heatsink	R_{thJ-hs}	DC operation single side cooled	0.042	K/W
		DC operation double side cooled	0.021	
Maximum thermal resistance, case to heatsink	R_{thC-hs}	DC operation single side cooled	0.006	
		DC operation double side cooled	0.003	
Mounting force, ± 10 %			24 500 (2500)	N (kg)
Approximate weight			425	g
Case style		See dimensions - link at the end of datasheet	K-PUK (A-24)	

 ΔR_{thJC} CONDUCTION

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION		TEST CONDITIONS	UNITS
	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE		
180°	0.003	0.003	0.002	0.002	$T_J = T_J$ maximum	K/W
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005		
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

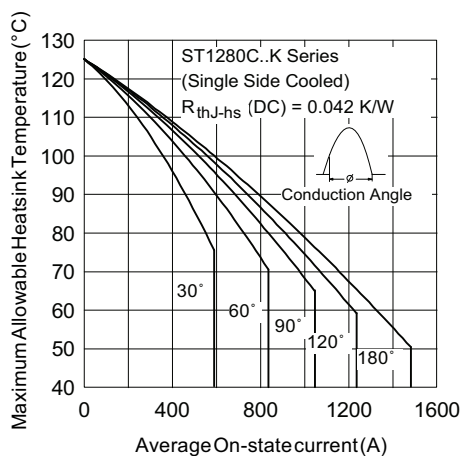


Fig. 1 - Current Ratings Characteristics

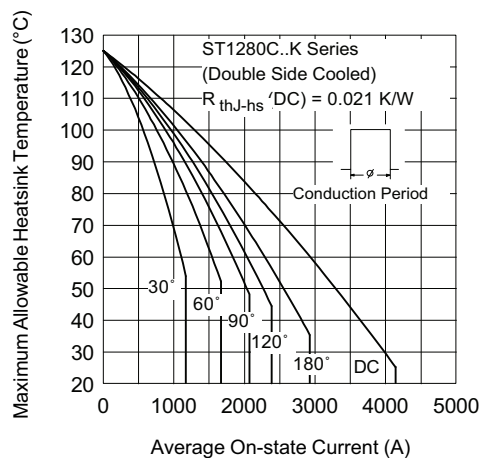


Fig. 4 - Current Ratings Characteristics

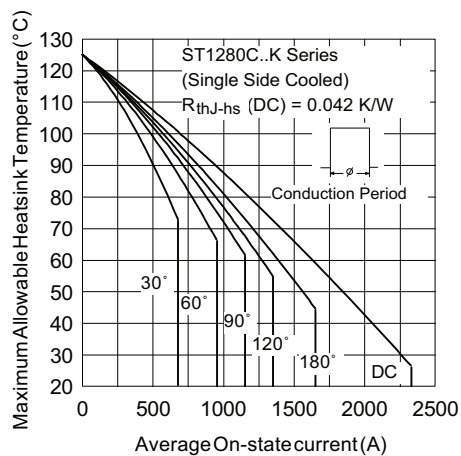


Fig. 2 - Current Ratings Characteristics

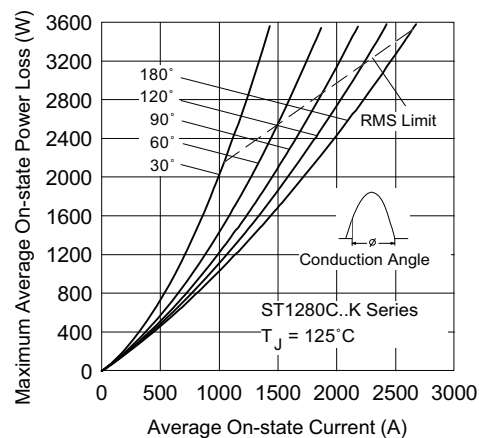


Fig. 5 - On-State Power Loss Characteristics

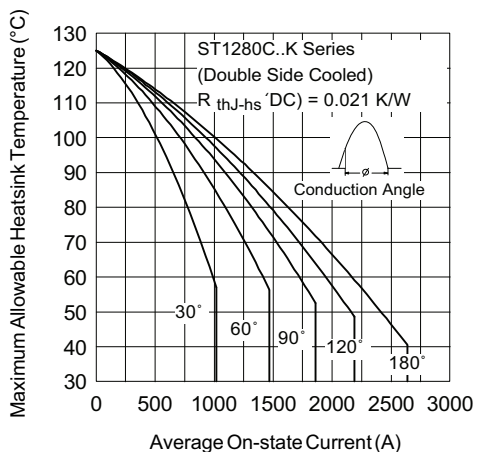


Fig. 3 - Current Ratings Characteristics

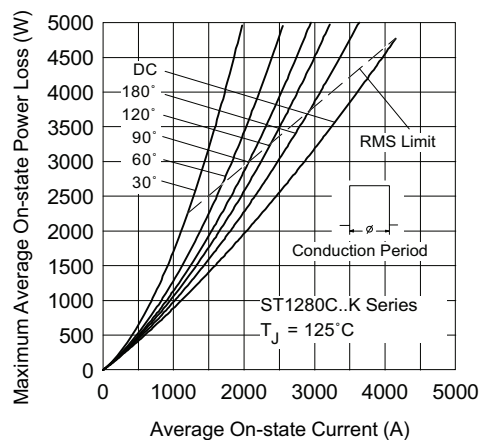


Fig. 6 - On-State Power Loss Characteristics

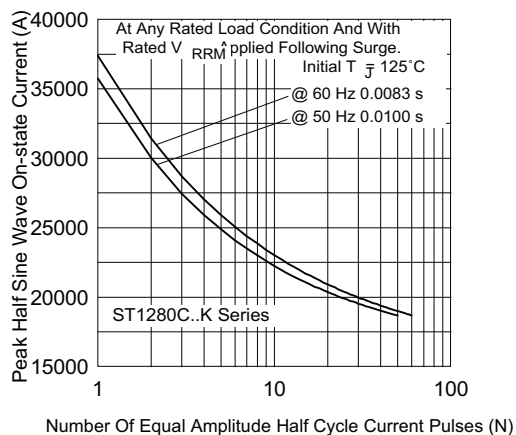


Fig. 7 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

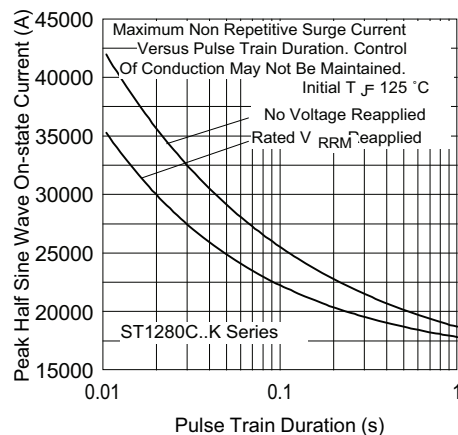


Fig. 8 - Maximum Non-Repetitive Surge Current Single and Double Side Cooled

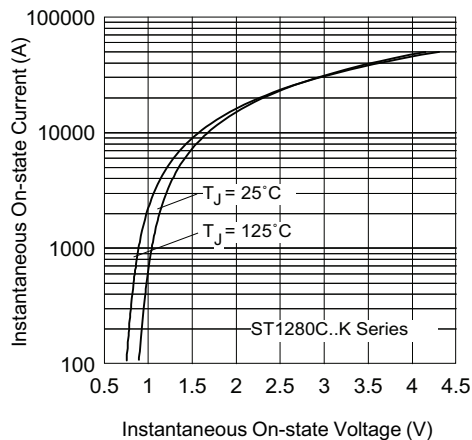


Fig. 9 - On-State Voltage Drop Characteristics

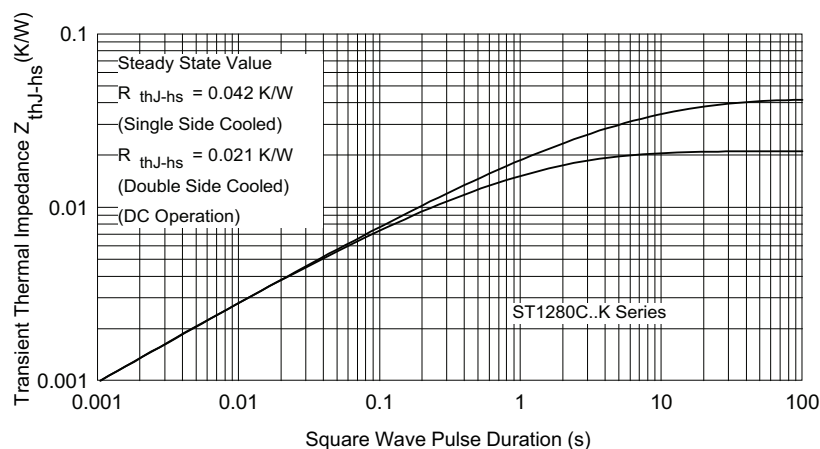


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

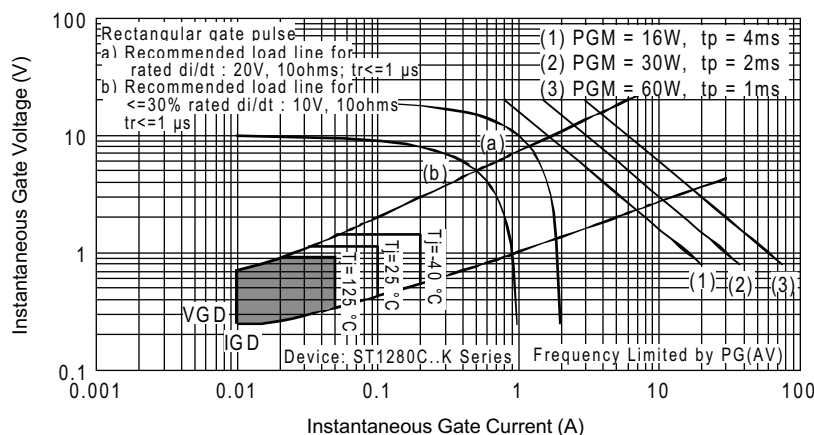


Fig. 11 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	ST	128	0	C	06	K	1	-
	(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)

- | | | |
|----------|---|---|
| 1 | - | Vishay Semiconductors product |
| 2 | - | Thyristor |
| 3 | - | Essential part number |
| 4 | - | 0 = converter grade |
| 5 | - | C = ceramic PUK |
| 6 | - | Voltage code x 100 = V_{RRM} (see Voltage Ratings table) |
| 7 | - | K = PUK case K-PUK (A-24) |
| 8 | - | 0 = eyelet terminals (gate and auxiliary cathode unsoldered leads) |
| | | 1 = fast-on terminals (gate and auxiliary cathode unsoldered leads) |
| | | 2 = eyelet terminals (gate and auxiliary cathode soldered leads) |
| | | 3 = fast-on terminals (gate and auxiliary cathode soldered leads) |
| 9 | - | Critical dV/dt : • none = 500 V/ μs (standard selection) |
| | | • L = 1000 V/ μs (special selection) |

LINKS TO RELATED DOCUMENTS

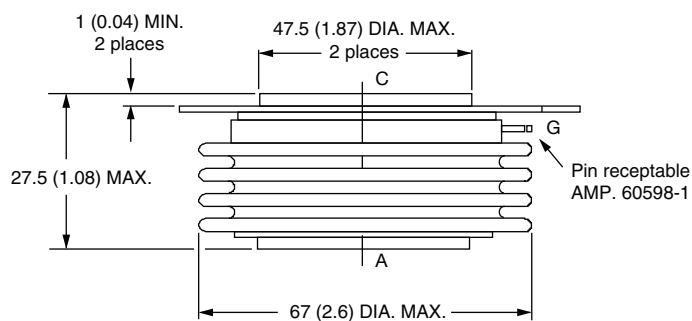
Dimensions	www.vishay.com/doc?95081
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K-PUK (A-24)

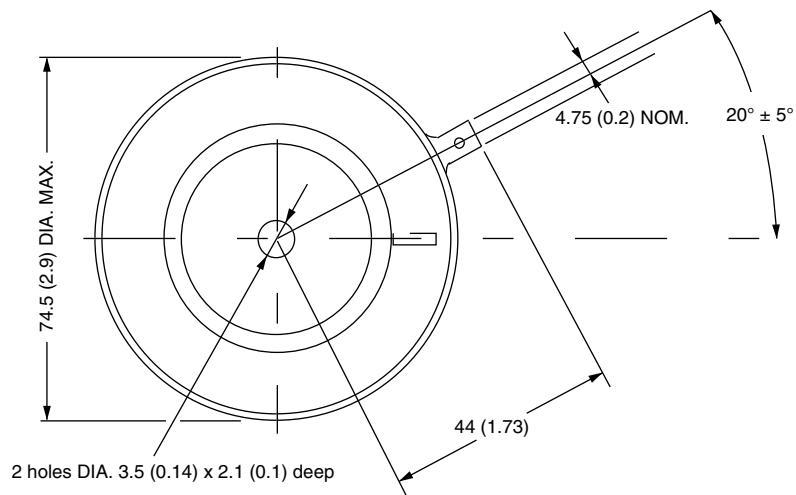
DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum
Strike distance: 17.99 (0.708) minimum



Note:

A = Anode
C = Cathode
G = Gate



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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